HFZT

3DD13001

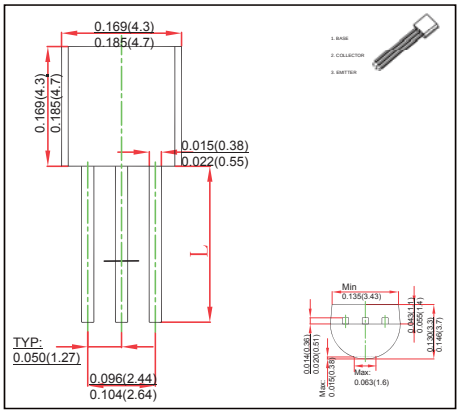
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Power switching applications
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbl	Value	Unit
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage	V_{CEO}	420	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current-Continuous	I_C	0.2	A
Collector Power Dissipation	P_C	0.75	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55-150	℃

Electrical Specification(T_A=25℃ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100uA, I_E=0	600			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1 m A , I_B=0	400			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100uA, I_C=0	7			V
Collector cut-off current	I_{CBO}	V_{CB}=600V, I_E=0			10	uA
Collector cut-off current	I_{CEO}	V_{CE}= 400V, I_B=0			10	uA
Emitter cut-off current	I_{EBO}	V_{EB}=9V, I_C=0			10	uA
DC current gain	$h_{FE(2)}$	V_{CE}=5V, I_C=20mA	10			
	$h_{FE(3)}$	V_{CE}= 2 0 V , I_C=20mA	10		40	
	$h_{FE(4)}$	V_{CE}=10V, I_C=0.25mA	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA, I_B=10mA			1	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=50mA, I_B=10mA			1.2	V
Transition frequency	f_T	V_{CE}=20V ,I_C=20mA,f=1MHZ	8			
Fall time	t_f	I_C=0.1A, UI9600			1	
Storage time	t_S				3	